TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT5G131

Strobe Flash Applications

Unit: mm

- 3-V gate drive voltage: $V_{GE} = 3.0 \text{ V (min)}$ (@IC = 130 A)
- Supplied in compact and thin package requires only a small mounting area
- 5th generation (trench gate structure) IGBT
- Enhancement-mode
- Peak collector current: IC = 130 A (max)

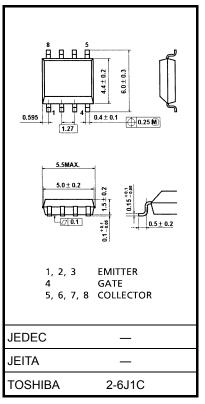
Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	400	V	
Gate-emitter voltage	DC	V_{GES}	±6	V	
	Pulse	V_{GES}	±8		
Collector current	DC	I _C	5	А	
	1 ms	I _{CP}	130		
Collector power dissipation (Note 1)		PC	1.1	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Note 1: Drive operation: Mount on glass epoxy board [1 inch $^2 \times 1.5 t$]

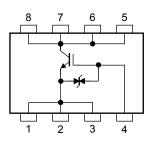
Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.080 g (typ.)

Equivalent Circuit



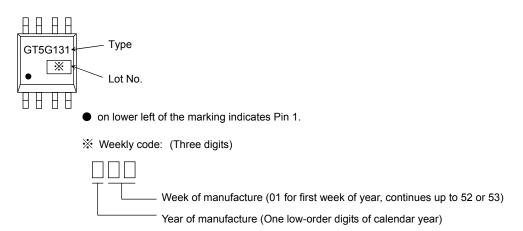
These devices are MOS type. Users should follow proper ESD handling procedures. Operating condition of turn-off dv/dt should be lower than 400 V/ μs .

Electrical Characteristics (Ta = 25°C)

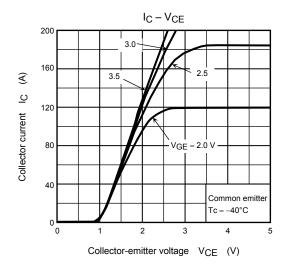
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	$V_{GE} = \pm 6 \text{ V}, V_{CE} = 0$	_	_	±10	μА
Collector cut-off cu	urrent	I _{CES}	V _{CE} = 400 V, V _{GE} = 0	_	_	10	μА
Gate-emitter cut-o	ff voltage	V _{GE} (OFF)	I _C = 1 mA, V _{CE} = 5 V	0.5	_	1.0	٧
Collector-emitter s	aturation voltage	V _{CE} (sat)	I _C = 130 A, V _{GE} = 3 V	_	2.2	7.0	V
Input capacitance		C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz	_	2800	_	pF
Switching time	Rise time	t _r	$\begin{array}{c} 3 \text{ V} \\ 0 \\ \end{array}$ $\begin{array}{c} 30 \Omega \\ \text{O} \\ \end{array}$ $\begin{array}{c} \text{CS} \\ \text{E} \\ \text{N} \\ \text{IN: } t_r \leq 100 \text{ ns} \\ t_f \leq 100 \text{ ns} \\ \text{Duty cycle} \leq 1\% \end{array}$	_	1.3		- μs
	Turn-on time	t _{on}			1.4		
	Fall time	t _f		_	1.5		
	Turn-off time	t _{off}		_	1.8		
Thermal resistanc	e (Note 2)	R _{th (j-a)}	_	_	_	114	°C/W

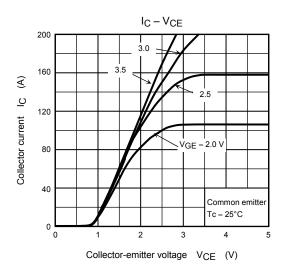
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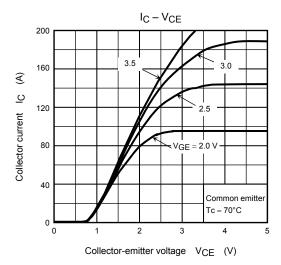
Marking

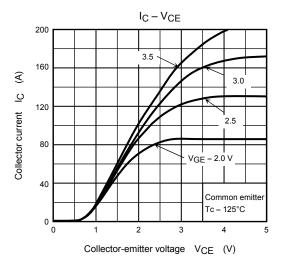


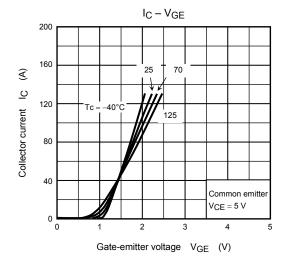
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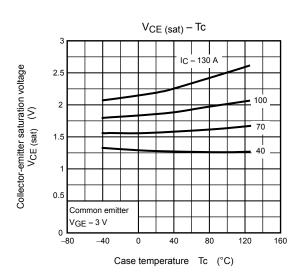




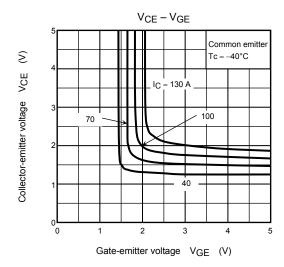


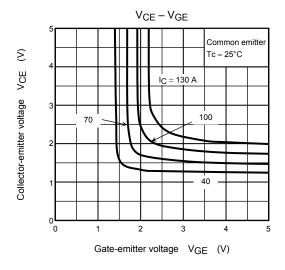


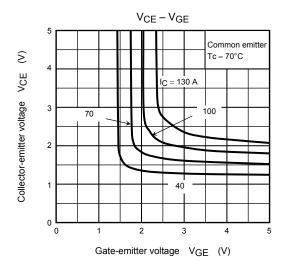


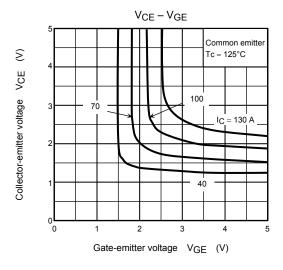


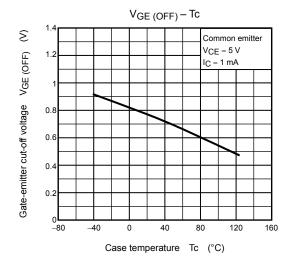
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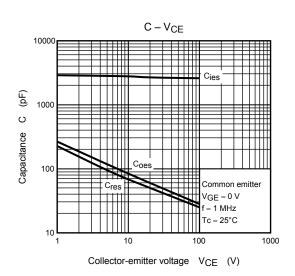


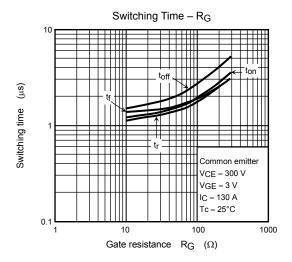


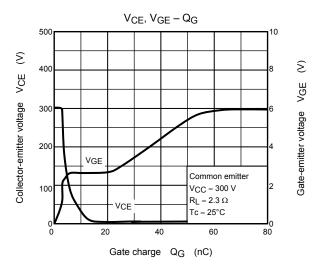


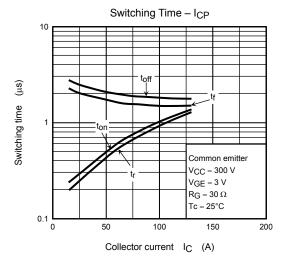


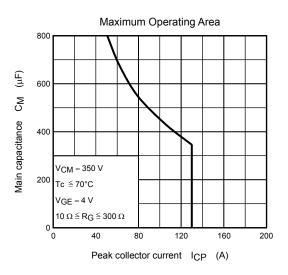


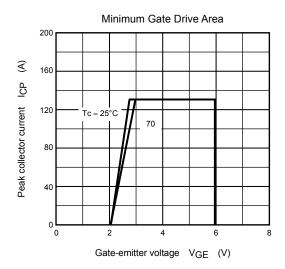












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